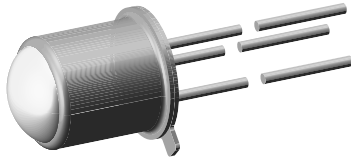


Silicon NPN Phototransistor, RoHS Compliant



94 8401

DESCRIPTION

BPW77 is a silicon NPN phototransistor with high radiant sensitivity in hermetically sealed TO-18 package with base terminal and glass lens. It is sensitive to visible and near infrared radiation.

FEATURES

- Package type: leaded
- Package form: TO-18
- Dimensions (in mm): Ø 4.7
- High photo sensitivity
- High radiant sensitivity
- Suitable for visible and near infrared radiation
- Fast response times
- Angle of half sensitivity: $\varphi = \pm 10^\circ$
- Base terminal connected
- Hermetically sealed package
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC



RoHS
COMPLIANT

APPLICATIONS

- Detector in electronic control and drive circuits

PRODUCT SUMMARY			
COMPONENT	I_{ca} (mA)	φ (deg)	$\lambda_{0.1}$ (nm)
BPW77NA	7.5 to 15	± 10	450 to 1080
BPW77NB	> 10	± 10	450 to 1080

Note

Test condition see table "Basic Characteristics"

ORDERING INFORMATION			
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
BPW77NA	Bulk	MOQ: 1000 pcs, 1000 pcs/bulk	TO-18
BPW77NB	Bulk	MOQ: 1000 pcs, 1000 pcs/bulk	TO-18

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Collector base voltage		V_{CBO}	80	V
Collector emitter voltage		V_{CEO}	70	V
Emitter base voltage		V_{EBO}	5	V
Collector current		I_C	50	mA
Collector peak current	$t_p/T = 0.5, t_p \leq 10$ ms	I_{CM}	100	mA
Total power dissipation	$T_{amb} \leq 25$ °C	P_V	250	mW
Junction temperature		T_j	125	°C
Operating temperature range		T_{amb}	- 40 to + 125	°C
Storage temperature range		T_{stg}	- 40 to + 125	°C
Soldering temperature	$t \leq 5$ s	T_{sd}	260	°C
Thermal resistance junction/ambient	Connected with Cu wire, 0.14 mm ²	R_{thJA}	400	K/W
Thermal resistance junction/gase		R_{thJC}	150	K/W

Note

$T_{amb} = 25$ °C, unless otherwise specified

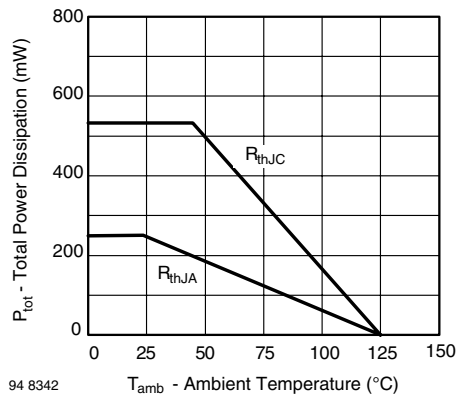


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector emitter breakdown voltage	$I_C = 1 \text{ mA}$	$V_{(BR)CEO}$	70			V
Collector emitter dark current	$V_{CE} = 20 \text{ V}, E = 0$	I_{CEO}		1	100	nA
Collector emitter capacitance	$V_{CE} = 5 \text{ V}, f = 1 \text{ MHz}, E = 0$	C_{CEO}		6		pF
Angle of half sensitivity		ϕ		± 10		deg
Wavelength of peak sensitivity		λ_p		850		nm
Range of spectral bandwidth		$\lambda_{0.1}$		450 to 1080		nm
Collector emitter saturation voltage	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, I_C = 1 \text{ mA}$	V_{CEsat}		0.15	0.3	V
Turn-on time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$	t_{on}		6		μs
Turn-off time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$	t_{off}		5		μs
Cut-off frequency	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$	f_c		110		kHz

Note

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

TYPE DEDICATED CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector light current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, V_{CE} = 5 \text{ V}$	BPW77NA	I_{ca}	7.5		15	mA
		BPW77NB	I_{ca}	10			mA

BASIC CHARACTERISTICS

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

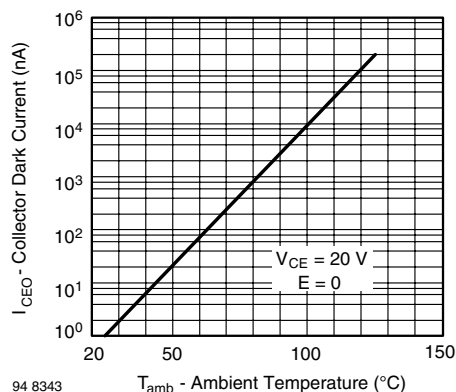


Fig. 2 - Collector Dark Current vs. Ambient Temperature

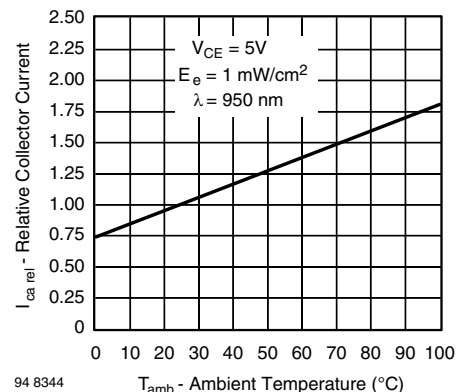


Fig. 3 - Relative Collector Current vs. Ambient Temperature

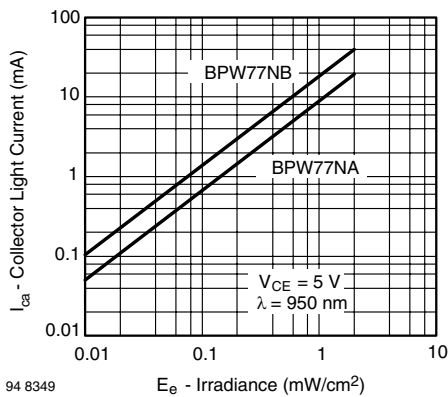


Fig. 4 - Collector Light Current vs. Irradiance

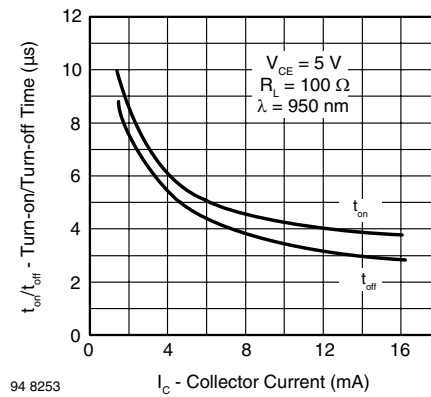


Fig. 7 - Turn-on/Turn-off Time vs. Collector Current

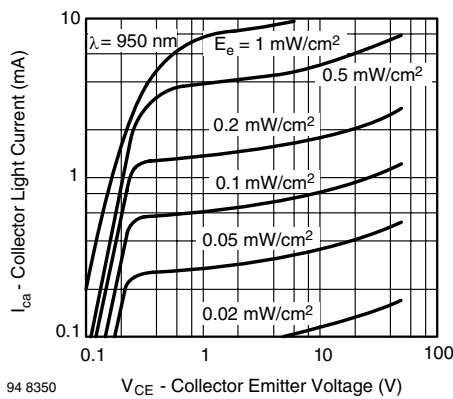


Fig. 5 - Collector Light Current vs. Collector Emitter Voltage

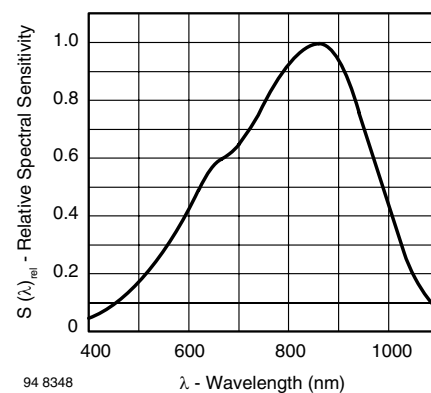


Fig. 8 - Relative Spectral Sensitivity vs. Wavelength

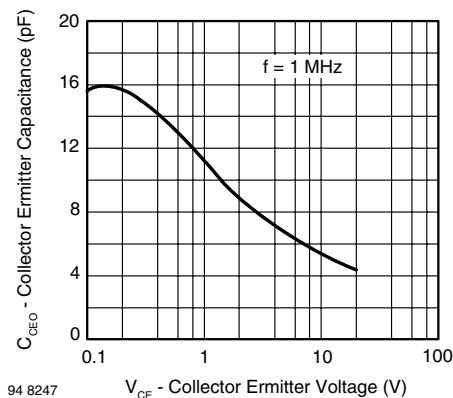


Fig. 6 - Collector Emitter Capacitance vs. Collector Emitter Voltage

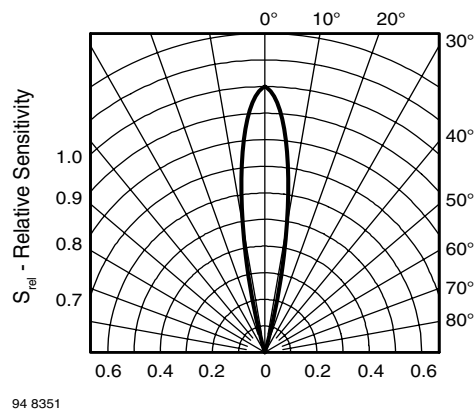


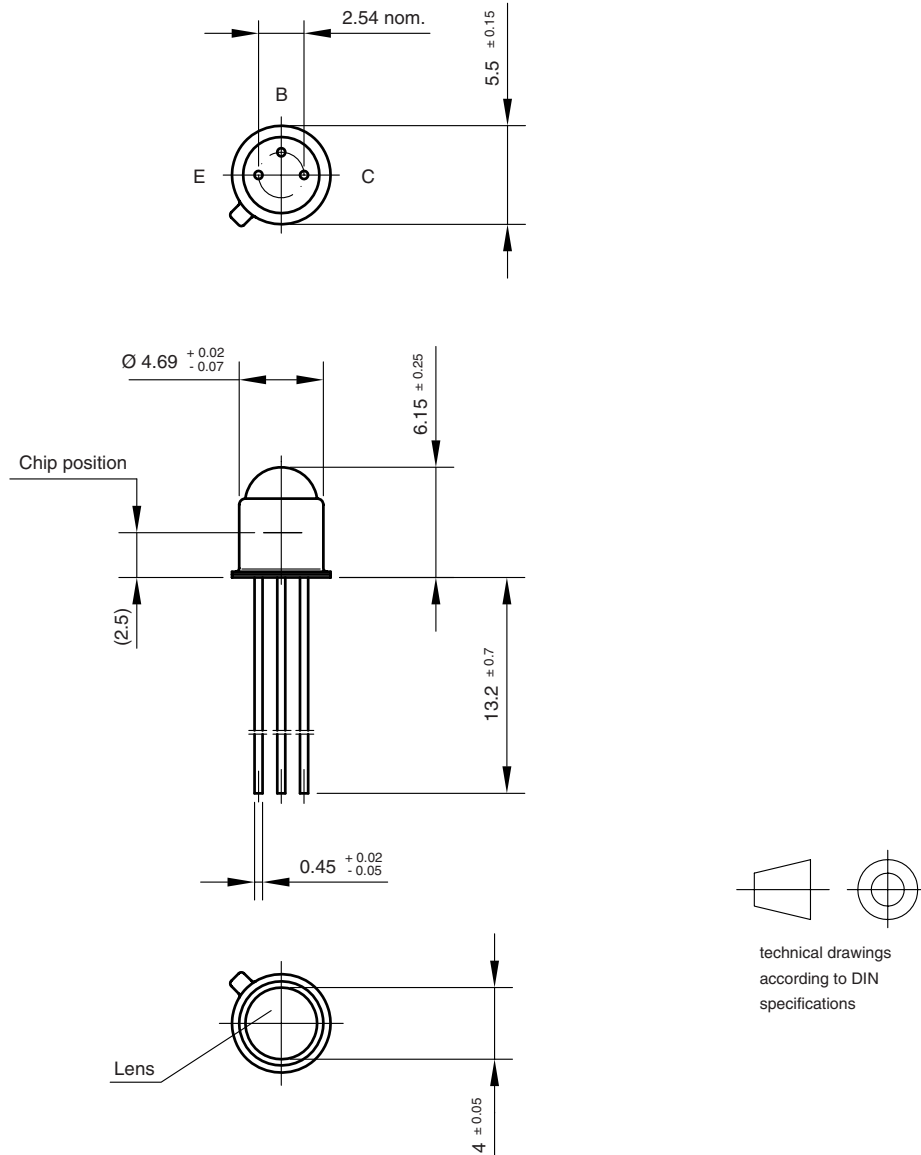
Fig. 9 - Relative Radiant Sensitivity vs. Angular Displacement



BPW77NA, BPW77NB

Silicon NPN Phototransistor, RoHS Compliant Vishay Semiconductors

PACKAGE DIMENSIONS in millimeters



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